

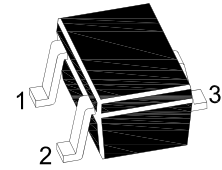
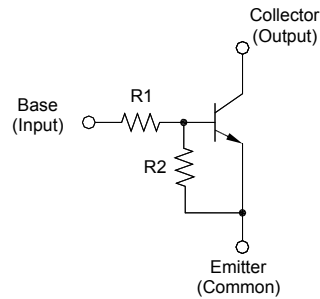
MMBTRC416E...MMBTRC422E

NPN Silicon Epitaxial Planar Transistor

for switching, interface circuit and drive circuit applications

Features

- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process



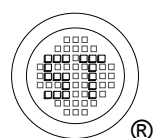
1.Base 2.Emitter 3.Collector
SOT-523 Plastic Package

Resistor Values

Type	R1 (K Ω)	R2 (K Ω)
MMBTRC416E	1	10
MMBTRC417E	2.2	2.2
MMBTRC418E	2.2	10
MMBTRC419E	4.7	10
MMBTRC420E	10	4.7
MMBTRC421E	47	10
MMBTRC422E	100	100

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter		Symbol	Value	Unit
Output Voltage		V_O	50	V
Input Voltage	MMBTRC416E	V_I	10, - 5	V
	MMBTRC417E		12, - 10	
	MMBTRC418E		12, - 5	
	MMBTRC419E		20, - 7	
	MMBTRC420E		30, - 10	
	MMBTRC421E		40, - 15	
	MMBTRC422E		40, - 10	
Output Current		I_O	100	mA
Total Power Dissipation		P_{tot}	100	mW
Junction Temperature		T_j	150	$^\circ\text{C}$
Storage Temperature Range		T_{stg}	- 55 to + 150	$^\circ\text{C}$

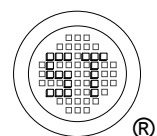


MMBTRC416E...MMBTRC422E

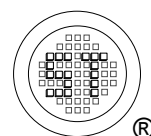
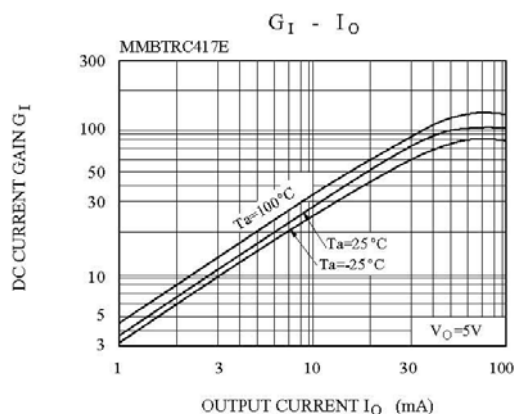
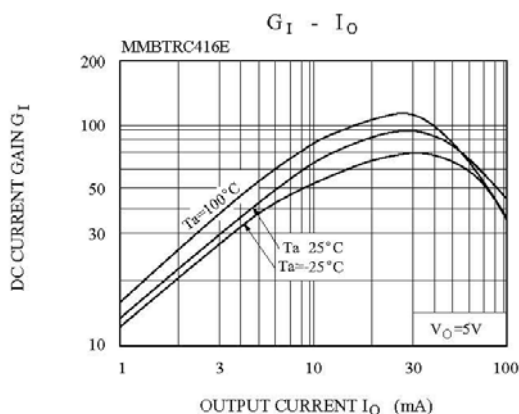
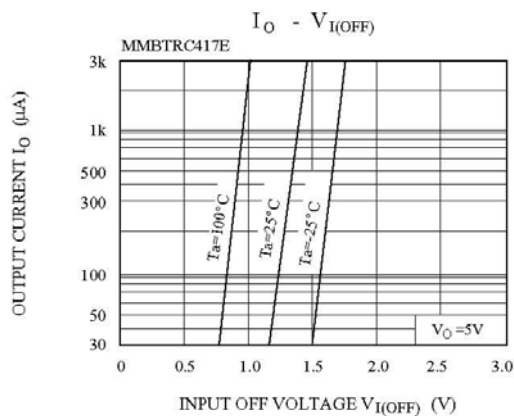
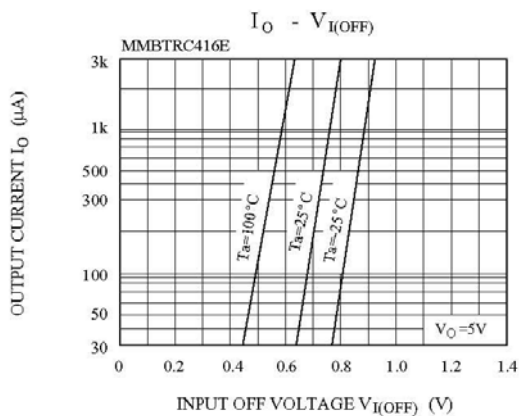
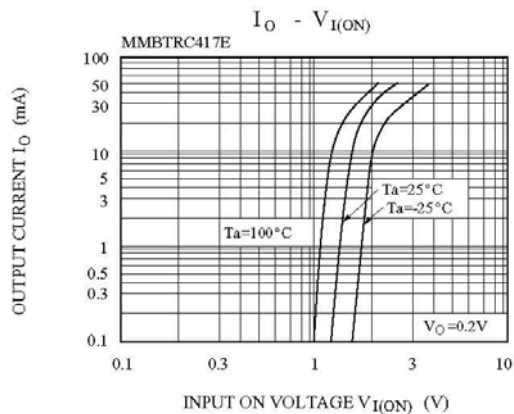
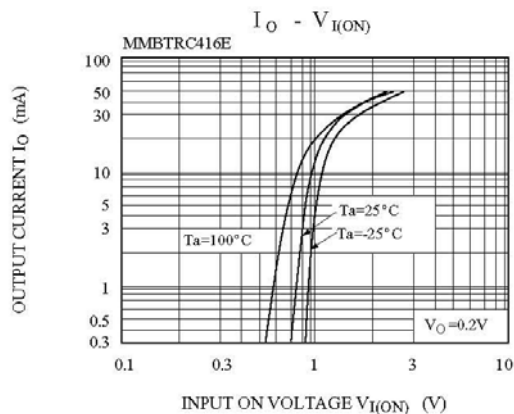
Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_O = 5\text{ V}$, $I_O = 5\text{ mA}$ at $V_O = 5\text{ V}$, $I_O = 20\text{ mA}$ at $V_O = 5\text{ V}$, $I_O = 10\text{ mA}$ at $V_O = 5\text{ V}$, $I_O = 10\text{ mA}$ at $V_O = 5\text{ V}$, $I_O = 10\text{ mA}$ at $V_O = 5\text{ V}$, $I_O = 5\text{ mA}$ at $V_O = 5\text{ V}$, $I_O = 5\text{ mA}$	MMBTRC416E MMBTRC417E MMBTRC418E MMBTRC419E MMBTRC420E MMBTRC421E MMBTRC422E	G_I 33 20 33 30 24 33 62	- - - - - - -	- - - - - - -	- - - - - - -
Output Cutoff Current at $V_O = 50\text{ V}$	$I_{O(OFF)}$	-	-	500	nA
Input Current at $V_I = 5\text{ V}$	MMBTRC416E MMBTRC417E MMBTRC418E MMBTRC419E MMBTRC420E MMBTRC421E MMBTRC422E	I_I - - - - - - -	- - - - - - -	7.2 3.8 3.8 1.8 0.88 0.16 0.15	mA
Output Voltage at $I_O = 10\text{ mA}$, $I_I = 0.5\text{ mA}$ at $I_O = 10\text{ mA}$, $I_I = 0.5\text{ mA}$ at $I_O = 10\text{ mA}$, $I_I = 0.5\text{ mA}$ at $I_O = 10\text{ mA}$, $I_I = 0.5\text{ mA}$ at $I_O = 10\text{ mA}$, $I_I = 0.5\text{ mA}$ at $I_O = 10\text{ mA}$, $I_I = 0.5\text{ mA}$ at $I_O = 5\text{ mA}$, $I_I = 0.25\text{ mA}$	MMBTRC416E MMBTRC417E MMBTRC418E MMBTRC419E MMBTRC420E MMBTRC421E MMBTRC422E	$V_{O(ON)}$ - - - - - - -	- - - - - - -	0.3 0.3 0.3 0.3 0.3 0.3 0.3	V
Input Voltage (ON) at $V_O = 0.3\text{ V}$, $I_O = 20\text{ mA}$ at $V_O = 0.3\text{ V}$, $I_O = 20\text{ mA}$ at $V_O = 0.3\text{ V}$, $I_O = 20\text{ mA}$ at $V_O = 0.3\text{ V}$, $I_O = 20\text{ mA}$ at $V_O = 0.3\text{ V}$, $I_O = 2\text{ mA}$ at $V_O = 0.3\text{ V}$, $I_O = 2\text{ mA}$ at $V_O = 0.3\text{ V}$, $I_O = 1\text{ mA}$	MMBTRC416E MMBTRC417E MMBTRC418E MMBTRC419E MMBTRC420E MMBTRC421E MMBTRC422E	$V_{I(ON)}$ - - - - - - -	- - - - - - -	3 3 3 2.5 3 5 3	V
Input Voltage (OFF) at $V_{CC} = 5\text{ V}$, $I_O = 100\text{ }\mu\text{A}$	MMBTRC416E MMBTRC417E MMBTRC418E MMBTRC419E MMBTRC420E MMBTRC421E MMBTRC422E	$V_{I(OFF)}$ 0.3 0.5 0.3 0.3 0.8 1 0.5	- - - - - - -	- - - - - - -	V
Transition Frequency at $V_O = 10\text{ V}$, $I_O = 5\text{ mA}$	f_T ¹⁾	-	250	-	MHz

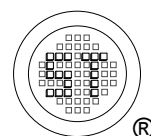
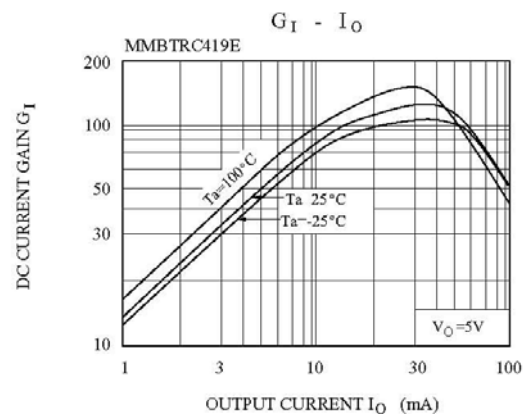
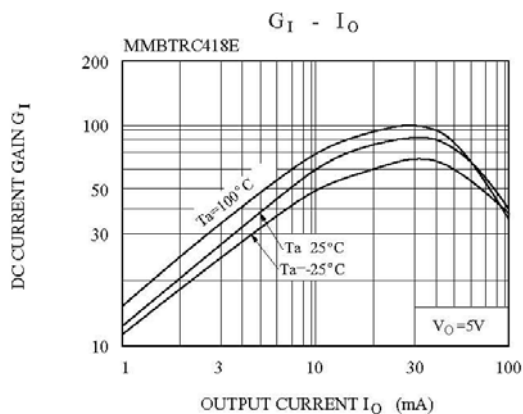
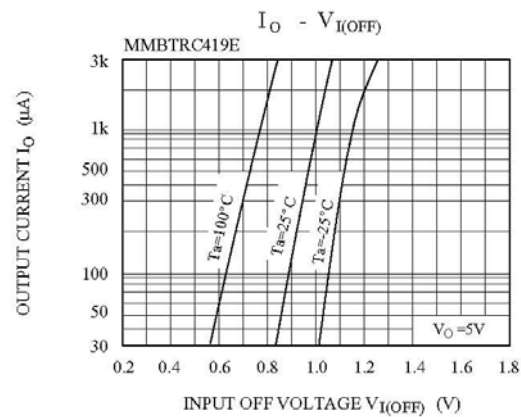
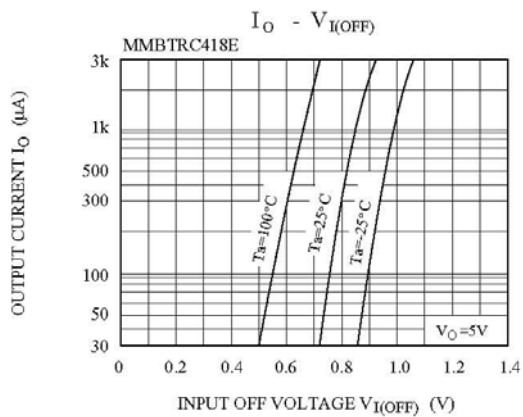
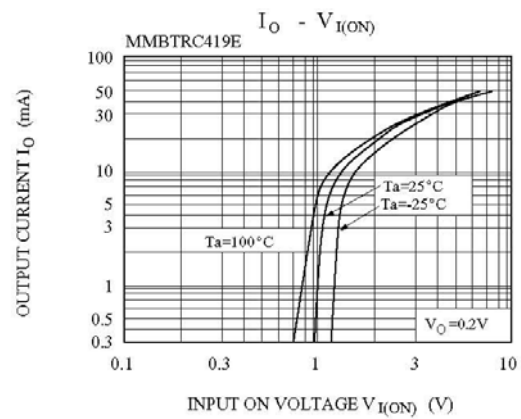
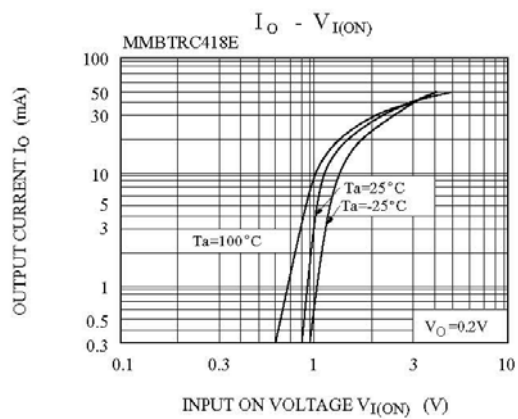
¹⁾ Characteristic of transistor only.



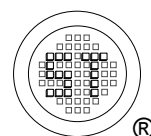
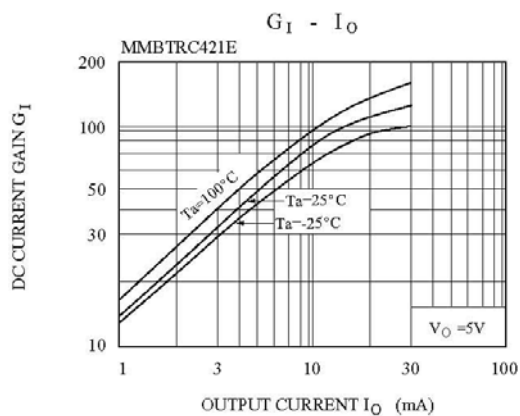
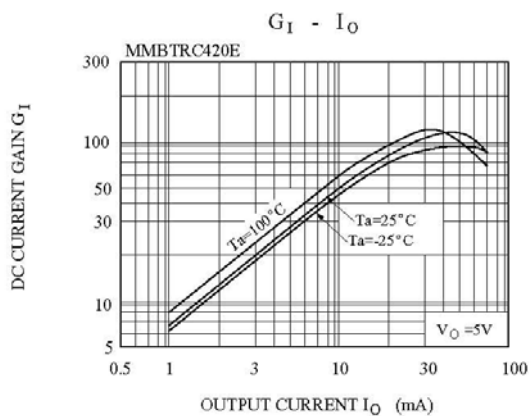
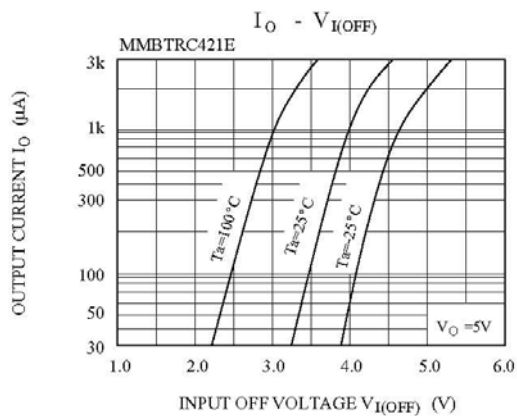
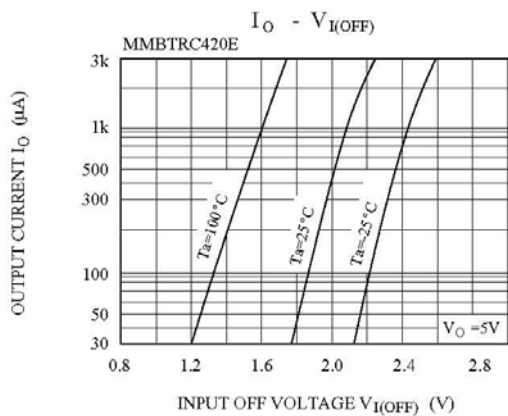
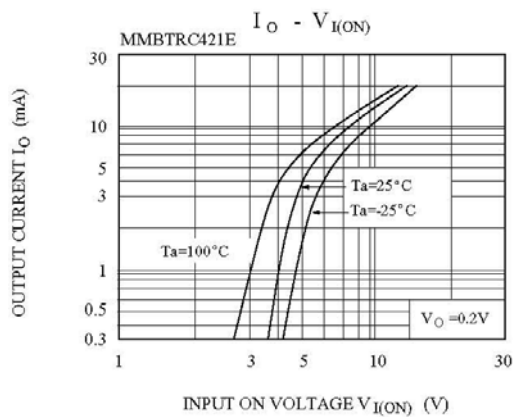
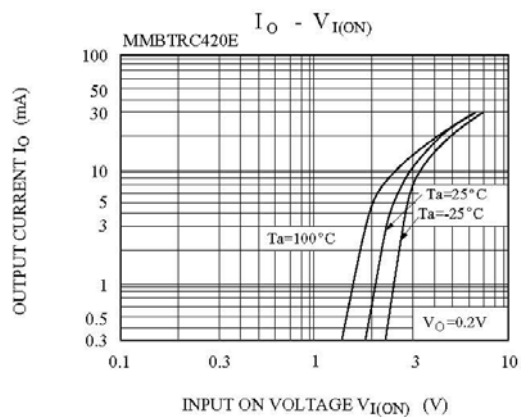
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